

Supporting Information

CdSe/ZnS core-shell quantum dots charge trapping layer for flexible photonic memory

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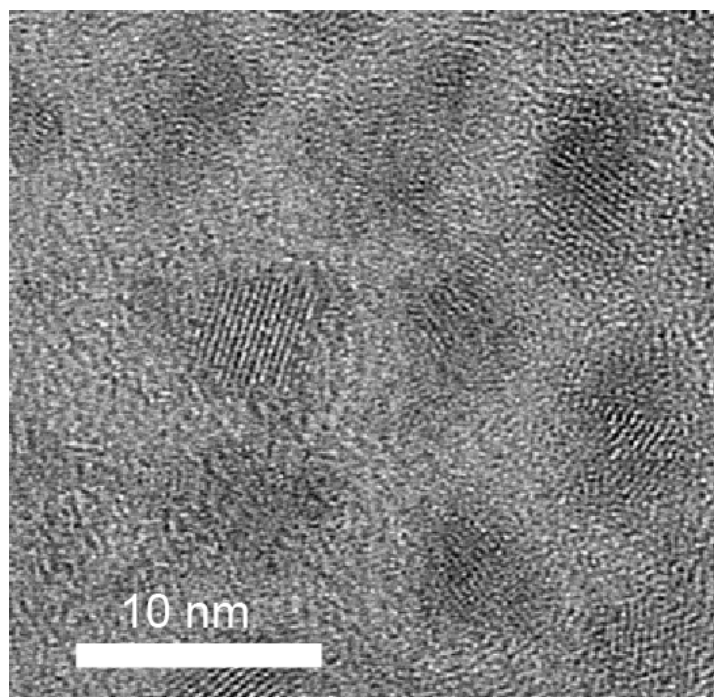


Fig. S1 HRTEM image of CdSe/ZnS core-shell NPs.

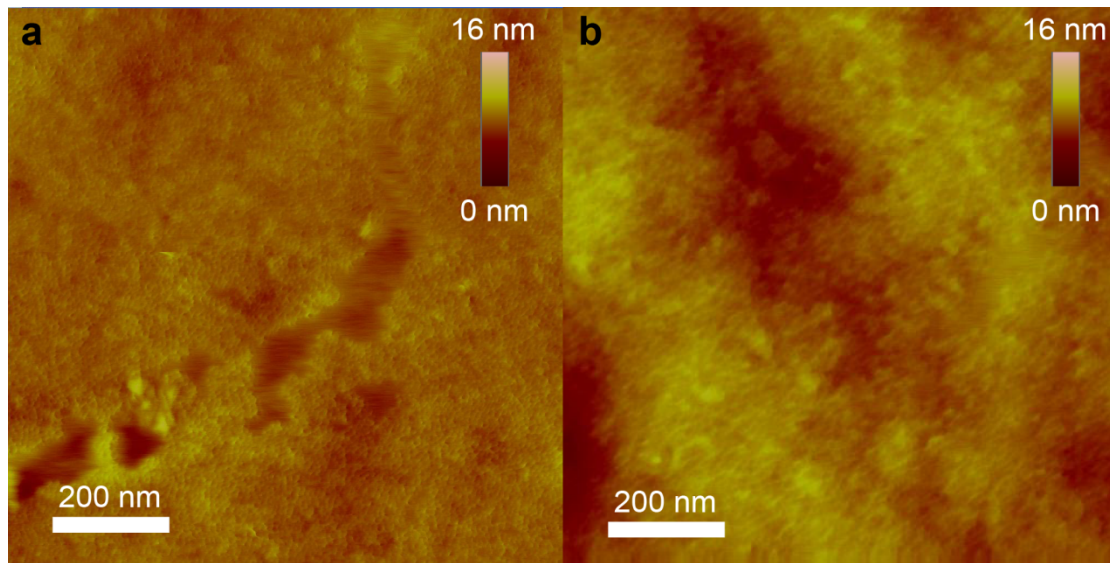


Fig. S2 The AFM images of CdSe/ZnS nanoparticles spin-coated onto (a) PVA layer and (b) Al₂O₃ layer.

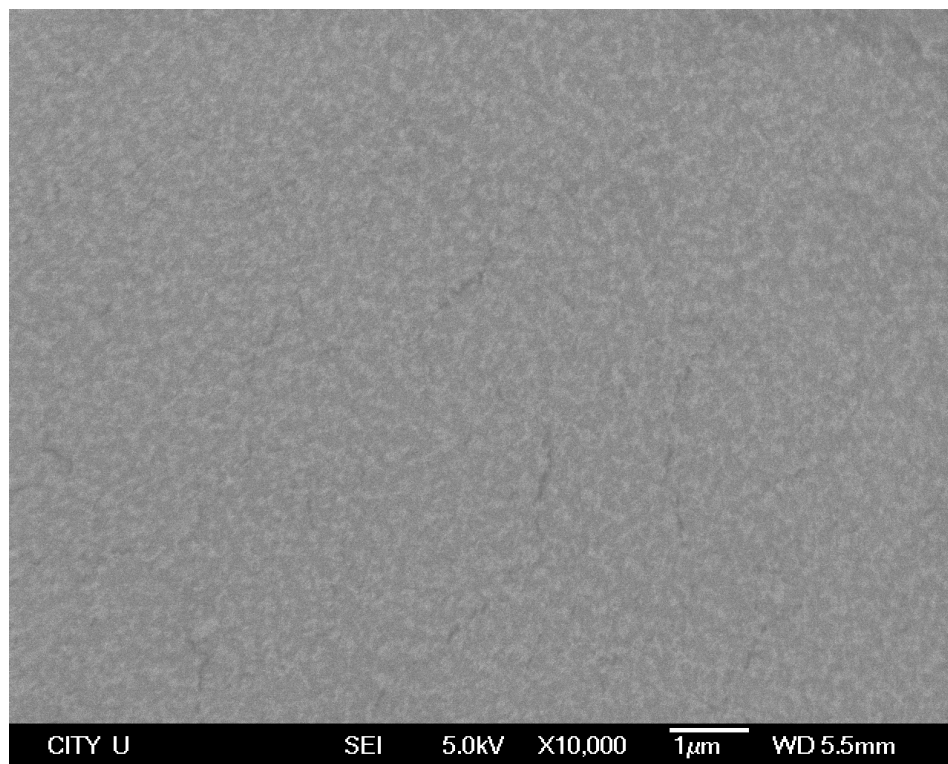


Fig. S3 The SEM images of CdSe/ZnS nanoparticles spin-coated onto PVA layer.

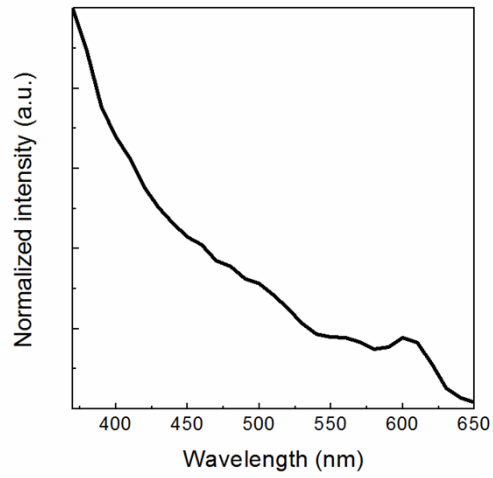


Figure S4. UV-visible absorption spectrum of CdSe/ZnS nanoparticle monolayer.

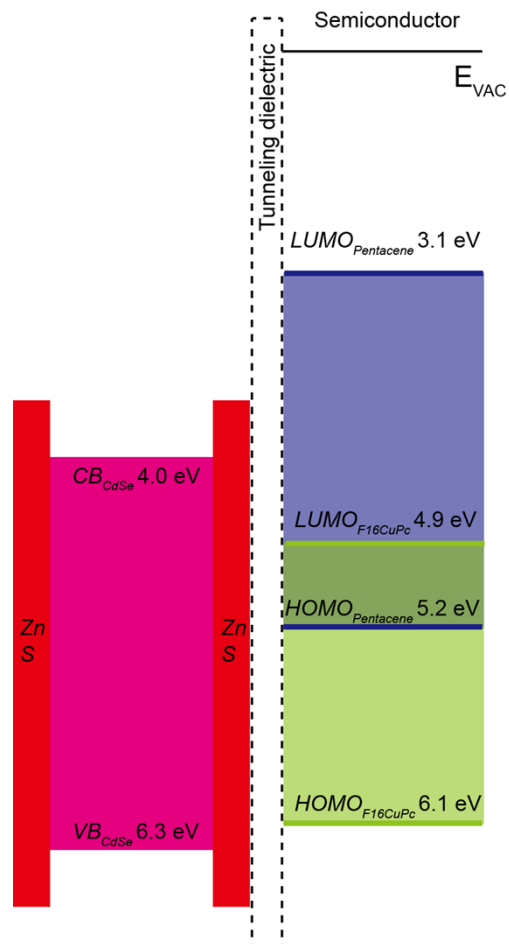


Figure S5. Energy level alignment of photonic memory devices.